

2SC3478
Rev.E Mar.-2016

KF \$0) E GE Silicon NPN transistor in a TO-92 Plastic Package.

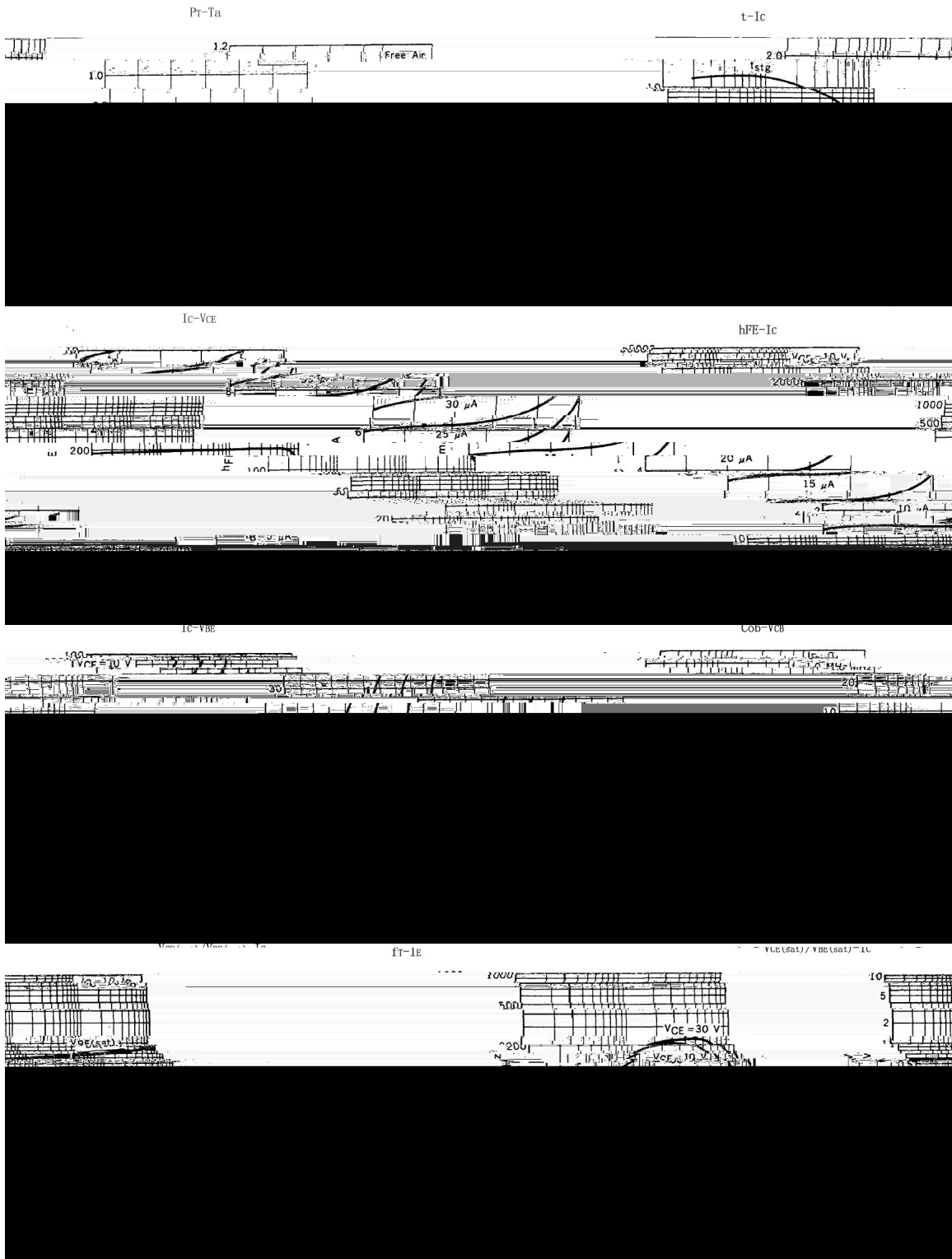
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High breakdown voltage, good h_{FE} linearity, complementary to 2SA1376.

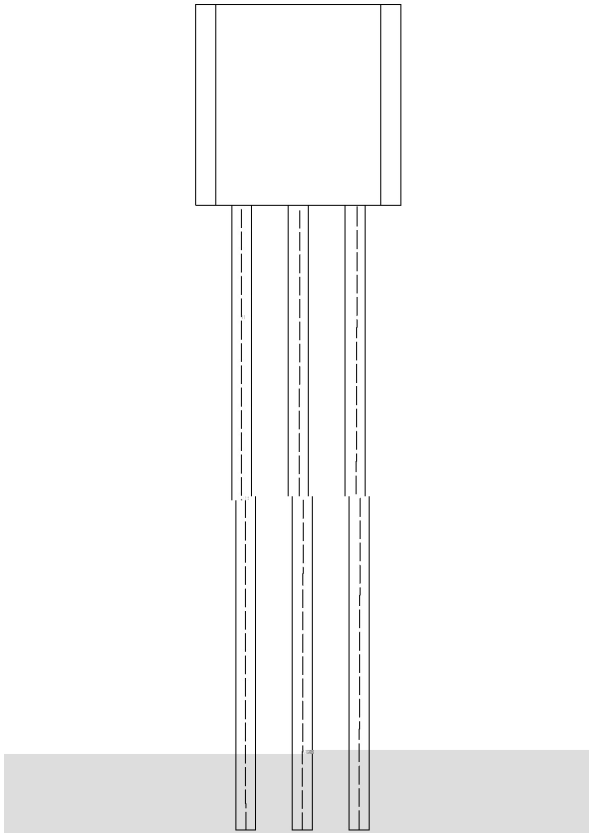
General purpose amplifier applications requiring high breakdown voltages.

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|--------|------|
| Collector to Base Voltage | V_{CBO} | 200 | V |
| Collector to Emitter Voltage | V_{CEO} | 180 | V |
| Emitter to Base Voltage | V_{EBO} | 5.0 | V |
| Collector Current - Continuous | I_C | 100 | mA |
| Collector Current – Continuous(Pulse) | I_{CP} | 200 | mA |
| Base Current - Continuous | I_B | 20 | mA |
| Collector Power Dissipation | P_C | 750 | mW |
| Junction Temperature | T_j | 150 | |
| Storage Temperature Range | T | | |

/ Electrical Characteristic Curve

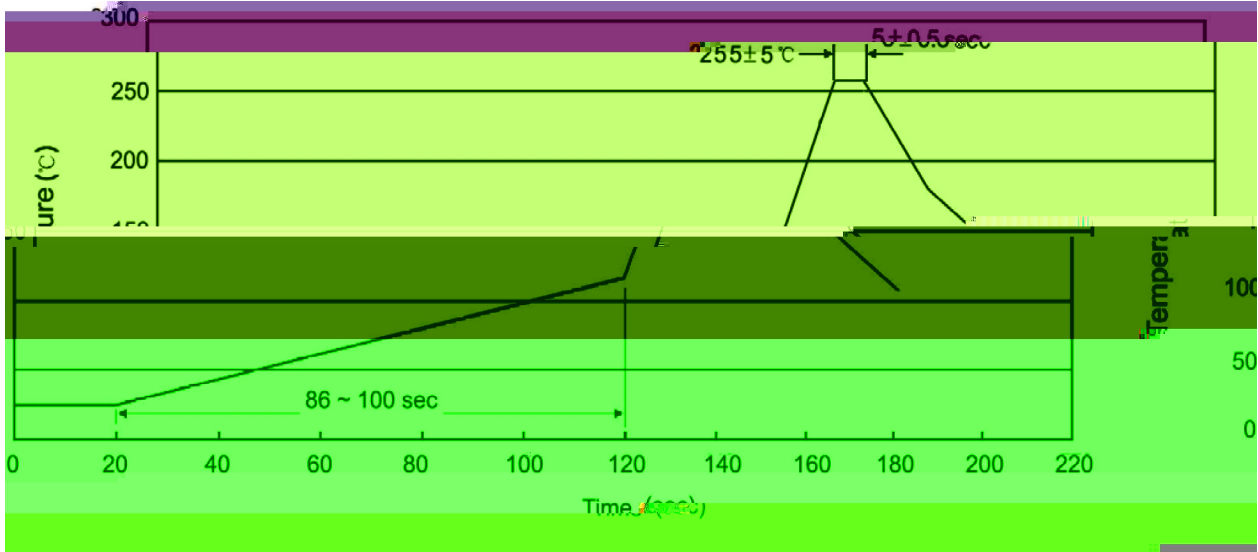


/ Marking Instructions



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Note:
BR: Company Code.
C3478: Product Type.
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() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5..0.5sec; | | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

| | | | |
|--------------|-------|-----------|------------|
| Package Type | Units | Dimension | (unit mm3) |
|--------------|-------|-----------|------------|